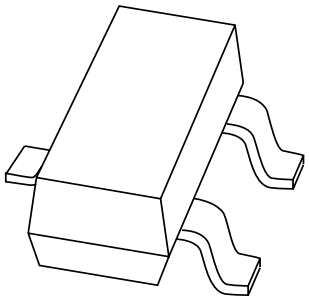
DATA SHEET



BAS19; BAS20; BAS21
General purpose diodes

Product data sheet
Supersedes data of 1999 May 26

2003 Mar 20

General purpose diodes BAS19; BAS20; BAS21

FEATURES

- Small plastic SMD package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 100 V; 150 V; 200 V
- Repetitive peak reverse voltage: max. 120 V; 200 V; 250 V
- Repetitive peak forward current: max. 625 mA.

APPLICATIONS

- General purpose switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS19, BAS20 and BAS21 are general purpose diodes fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE (1)
BAS19	JP∗
BAS20	JR∗
BAS21	JS∗

Note

1. ∗ = p: Made in Hong Kong.
   ∗ = t: Made in Malaysia.
   ∗ = W: Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode

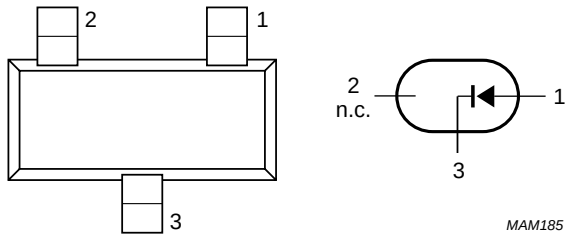


Fig.1 Simplified outline (SOT23) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BAS19		–	120	V
	BAS20		–	200	V
	BAS21		–	250	V
V_R	continuous reverse voltage				
	BAS19		–	100	V
	BAS20		–	150	V
	BAS21		–	200	V
I_F	continuous forward current	see Fig.2; note 1	–	200	mA
I_{FRM}	repetitive peak forward current		–	625	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	–	9	A
		t = 100 μs	–	3	A
		t = 10 ms	–	1.7	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.3		
		I_F = 100 mA	1	V
		I_F = 200 mA	1.25	V
I_R	reverse current	see Fig.5		
	BAS19	V_R = 100 V	100	nA
		V_R = 100 V; T_j = 150 °C	100	μA
	BAS20	V_R = 150 V	100	nA
		V_R = 150 V; T_j = 150 °C	100	μA
	BAS21	V_R = 200 V	100	nA
		V_R = 200 V; T_j = 150 °C	100	μA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	5	pF
t_{rr}	reverse recovery time	when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA; see Fig.8	50	ns

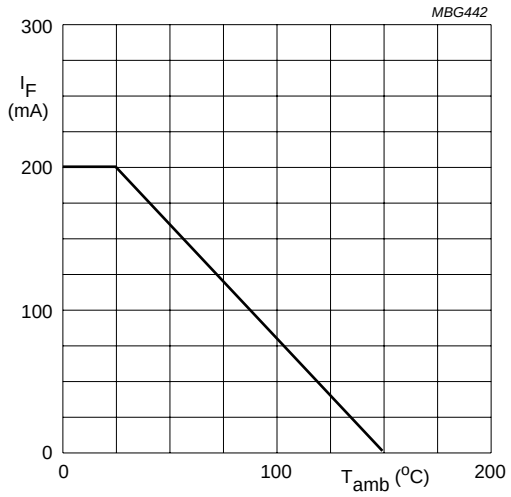
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point		330	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

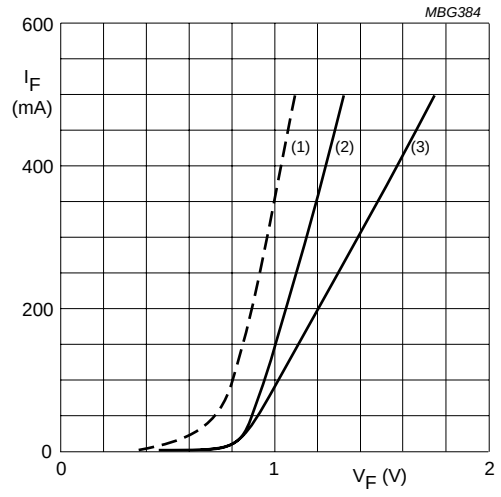
1. Device mounted on an FR4 printed-circuit board.

GRAPHICAL DATA



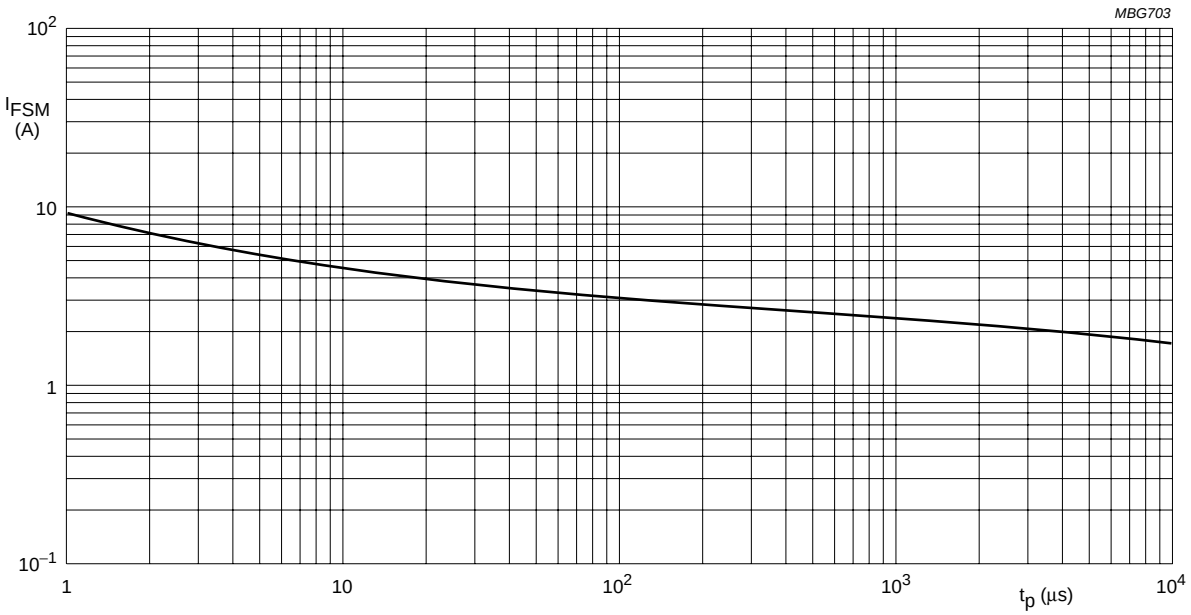
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



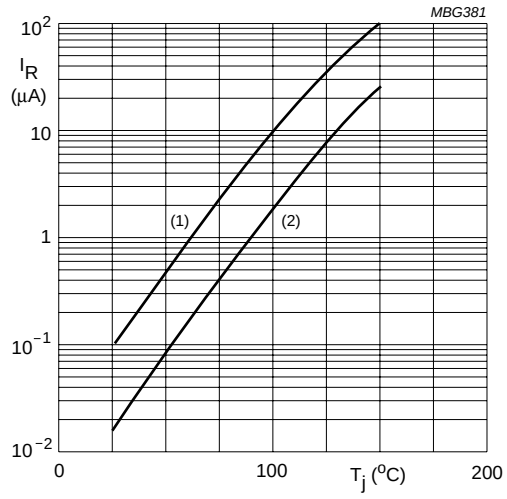
(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



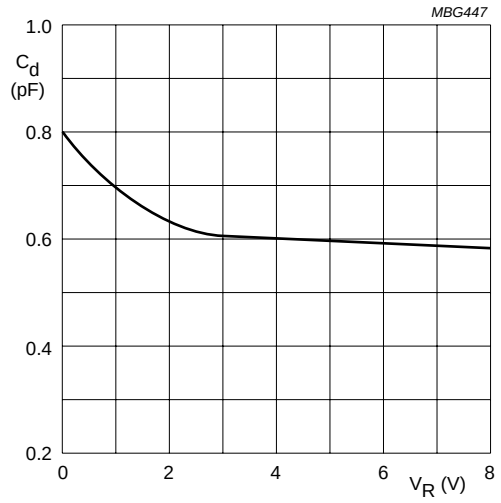
Based on square wave currents.
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.



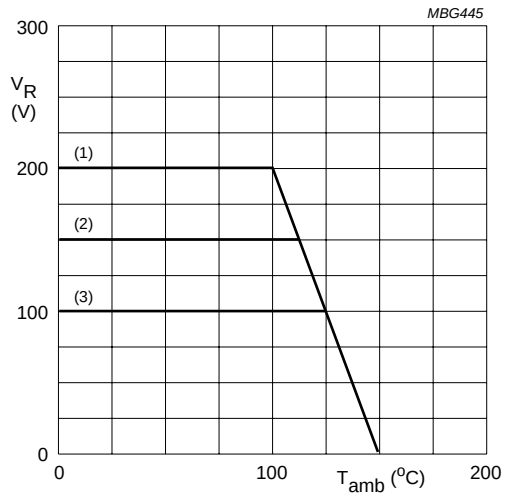
(1) $V_R = V_{Rmax}$; maximum values.
(2) $V_R = V_{Rmax}$; typical values.

Fig.5 Reverse current as a function of junction temperature.



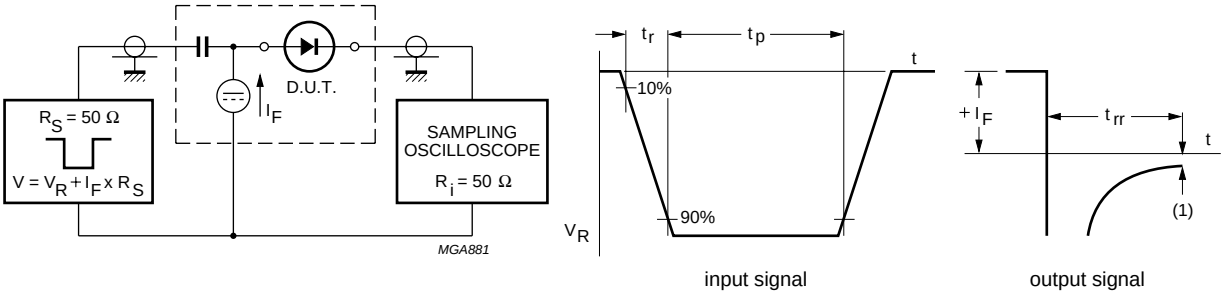
f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.



(1) BAS21.
(2) BAS20.
(3) BAS19.

Fig.7 Maximum permissible continuous reverse voltage as a function of the ambient temperature.

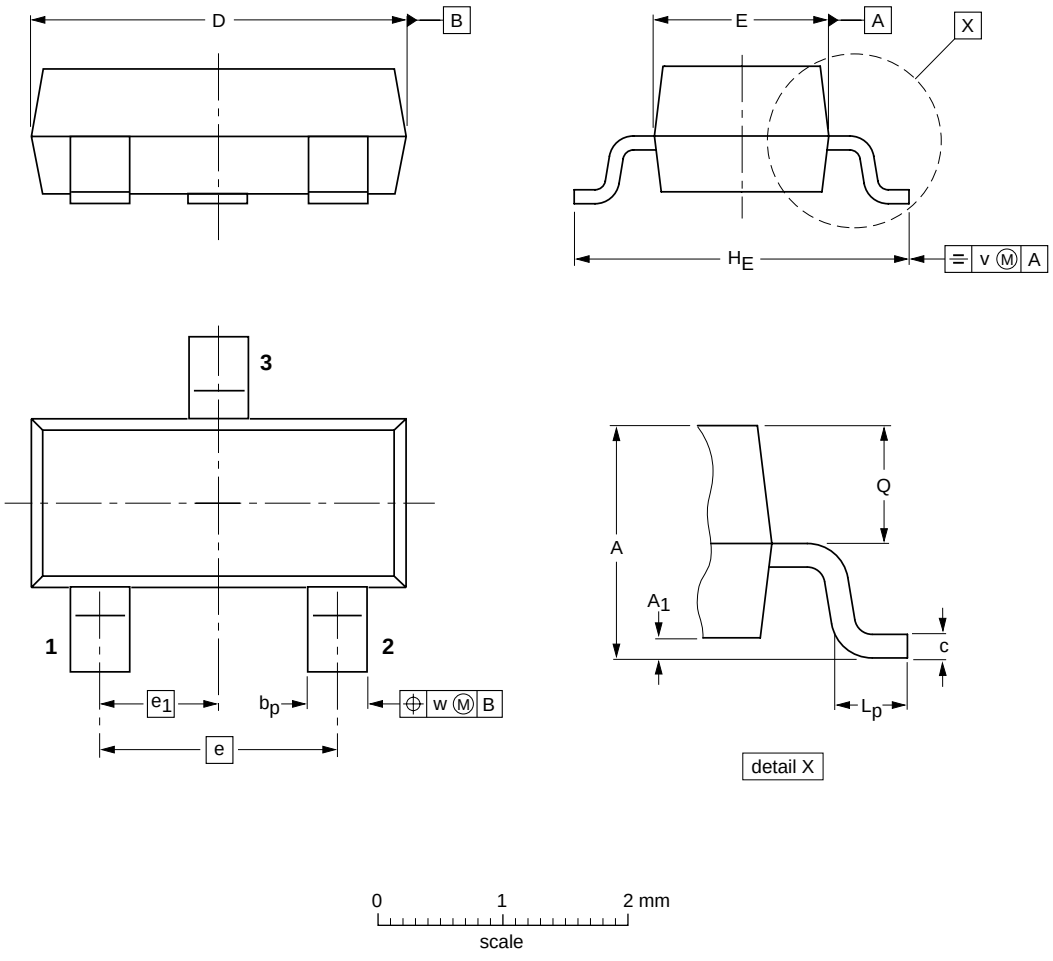


(1) I_R = 3 mA.

Fig.8 Reverse recovery voltage test circuit and waveforms.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				~~97-02-28~~ 99-09-13

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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